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April 1<sup>st</sup>, 2010 Renesas Electronics Corporation

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# MOS FIELD EFFECT TRANSISTOR $\mu PA1807$

### N-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

#### **DESCRIPTION**

The  $\mu$ PA1807 is a switching device, which can be driven directly by a 4.0 V power source.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as DC/DC converters and power management of notebook computers and so on.

#### **FEATURES**

- 4.0 V drive available
- · Low on-state resistance

 $R_{DS(on)1} = 10 \text{ m}\Omega \text{ MAX.} (V_{GS} = 10 \text{ V}, I_D = 6.0 \text{ A})$ 

 $RDS(on)2 = 14 \text{ m}\Omega \text{ MAX.} (VGS = 4.5 \text{ V}, ID = 6.0 \text{ A})$ 

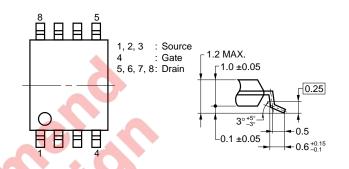
 $R_{DS(on)3} = 16 \text{ m}\Omega \text{ MAX.} \text{ (Vgs} = 4.0 \text{ V, ID} = 6.0 \text{ A)}$ 

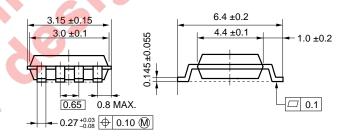
• Built-in G-S protection diode against ESD

### **ORDERING INFORMATION**

PART NUMBER	PACKAGE
μPA1807GR-9JG	Power TSSOP8

### PACKAGE DRAWING (Unit: mm)

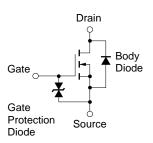




### ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs = 0 V)	VDSS	30	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±20	V
Drain Current (DC) (T <sub>A</sub> = 25°C)	ID(DC)	±12	Α
Drain Current (pulse) Note1	ID(pulse)	±48	Α
Total Power Dissipation Note2	Рт	2.0	W
Channel Temperature	Tch	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

### **EQUIVALENT CIRCUIT**



**Notes 1.** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

2. Mounted on ceramic substrate of 5000 mm<sup>2</sup> x 1.1 mm

**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

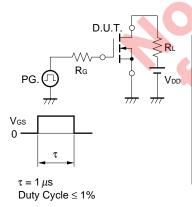
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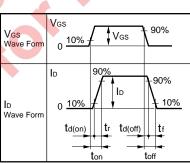


**ELECTRICAL CHARACTERISTICS (TA = 25°C)** 

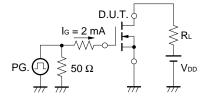
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	Inss	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V			1.0	μΑ
Gate Leakage Current	Igss	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V			±10	μΑ
Gate Cut-off Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.0 mA	1.5	2.0	2.5	V
Forward Transfer Admittance	<b>y</b> fs	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 6.0 A	7.0	15		S
Drain to Source On-state Resistance	RDS(on)1	Vgs = 10 V, ID = 6.0 A		8.1	10	mΩ
	R <sub>DS(on)2</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 6.0 A		10.5	14	mΩ
	RDS(on)3	V <sub>GS</sub> = 4.0 V, I <sub>D</sub> = 6.0 A		12	16	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> = 10 V		1000		pF
Output Capacitance	Coss	V <sub>GS</sub> = 0 V		390		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		140		pF
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 15 V, I <sub>D</sub> = 6.0 A		16		ns
Rise Time	tr	Vgs = 10 V		11		ns
Turn-off Delay Time	t <sub>d(off)</sub>	R <sub>G</sub> = 10 Ω		46		ns
Fall Time	<b>t</b> f			11.5		ns
Total Gate Charge	Qg	V <sub>DD</sub> = 24 V		19		nC
Gate to Source Charge	Qgs	Vgs = 10 V		3.1		nC
Gate to Drain Charge	Q <sub>GD</sub>	lo = 12 A		5.0		nC
Body Diode Forward Voltage	V <sub>F(S-D)</sub>	IF = 12 A, VGS = 0 V		0.82		V
Reverse Recovery Time	trr	IF = 12 A, VGS = 0 V		32		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		24		nC

### TEST CIRCUIT 1 SWITCHING TIME

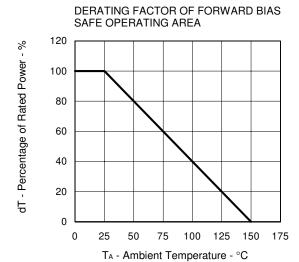




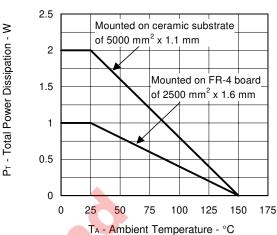
### **TEST CIRCUIT 2 GATE CHARGE**



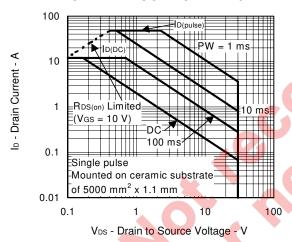
### TYPICAL CHARACTERISTICS (TA = 25°C)

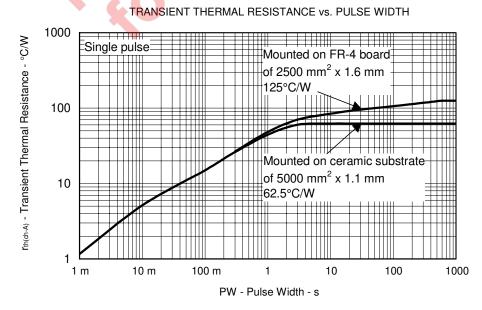


## TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



#### FORWARD BIAS SAFE OPERATING AREA



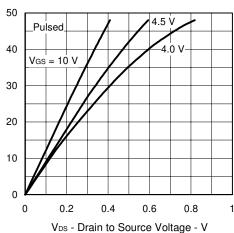


3

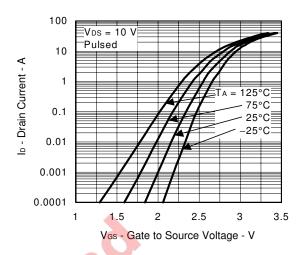
lo - Drain Current - A

VGS(off) - Gate Cut-off Voltage - V

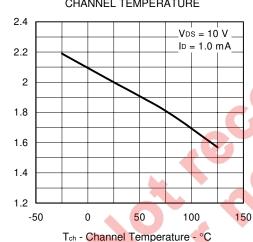
### DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



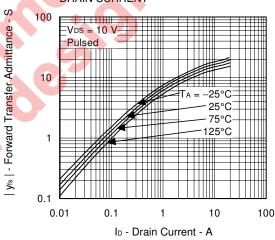
#### FORWARD TRANSFER CHARACTERISTICS



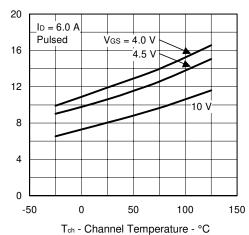
### GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



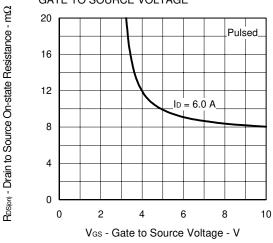
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



### DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



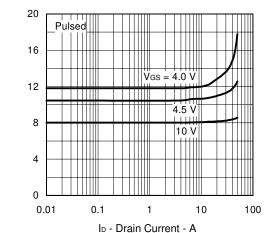
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



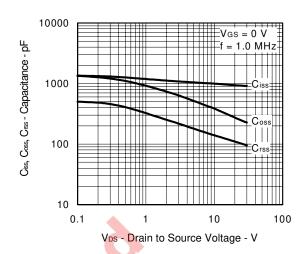
RDS(on) - Drain to Source On-state Resistance - mΩ

RDS(cn) - Drain to Source On-state Resistance - mΩ

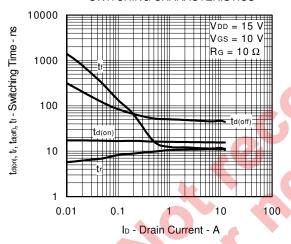
### DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



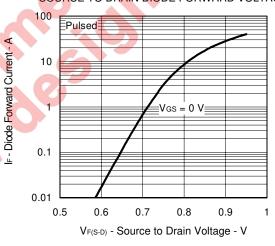
### CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



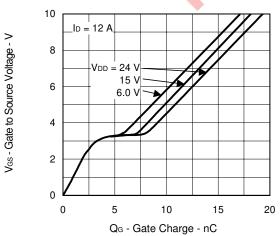
### SWITCHING CHARACTERISTICS



### SOURCE TO DRAIN DIODE FORWARD VOLTAGE



### DYNAMIC INPUT/OUTPUT CHARACTERISTICS



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